

0.8 μm SLD Module AS8E210GP30M

AS8E210GP30M is SLD (Super Luminescent Diode) module developed as incoherent light sources for various optical measurements. The device emits wide spectral incoherent light with high optical output power from PMF (polarization-maintaining fiber).

FEATURES

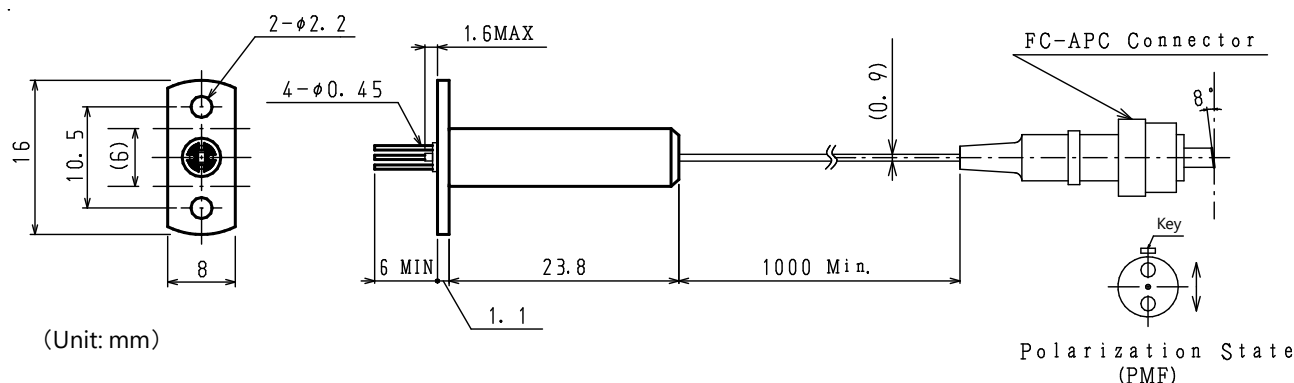
- Optical Output Power : 1 mW
- Spectral Bandwidth : 15 nm typ.
- Uncooled cylindrical type
- Built-in monitor photodiode

APPLICATION

- Optical sensing / Optical encoder
- Optical Coherent Tomography (OCT)
- Optical measurement

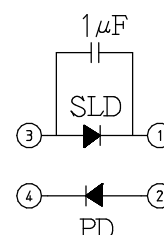
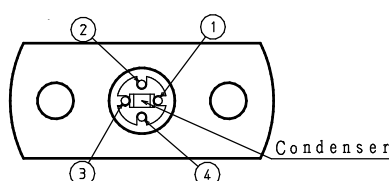


DIMENSIONS



PIN CONFIGURATION

No.	FUNCTION
1	SLD Cathode
2	PD Anode
3	SLD Anode
4	PD Cathode (case)



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
Output Power	P_f	1.2	mW
SLD Forward Current	I_F	120	mA
SLD Reverse Voltage	V_R	2	V
PD Reverse Voltage	V_{RD}	15	V
Operating Case Temperature	T_C	-20 to +70	°C
Storage Temperature	T_{stg}	-40 to +80	°C

*Excess over the absolute maximum ratings may cause device failure.

OPTICAL FIBER CHARACTERISTICS

Item	Min.	Typ.	Max.	Unit
Cut-off Wavelength	700	730	760	nm
Mode Field Diameter @850 nm	4.5	5.0	5.5	μm
Clad Diameter	123.5	125	126.5	μm
Coating Diameter	850	–	950	μm
Fiber Bending Radius	13	–	–	mm

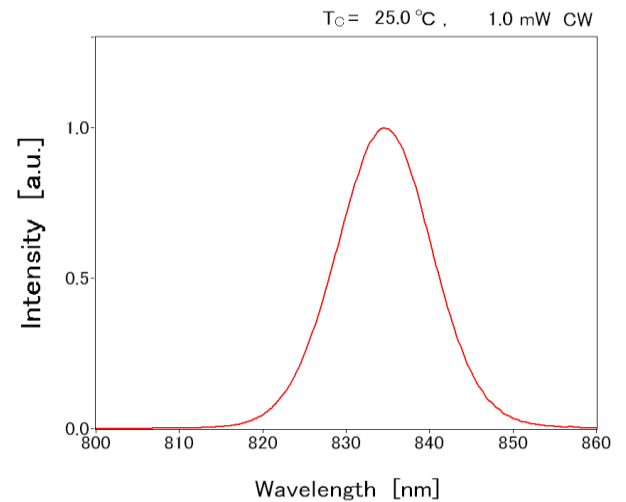
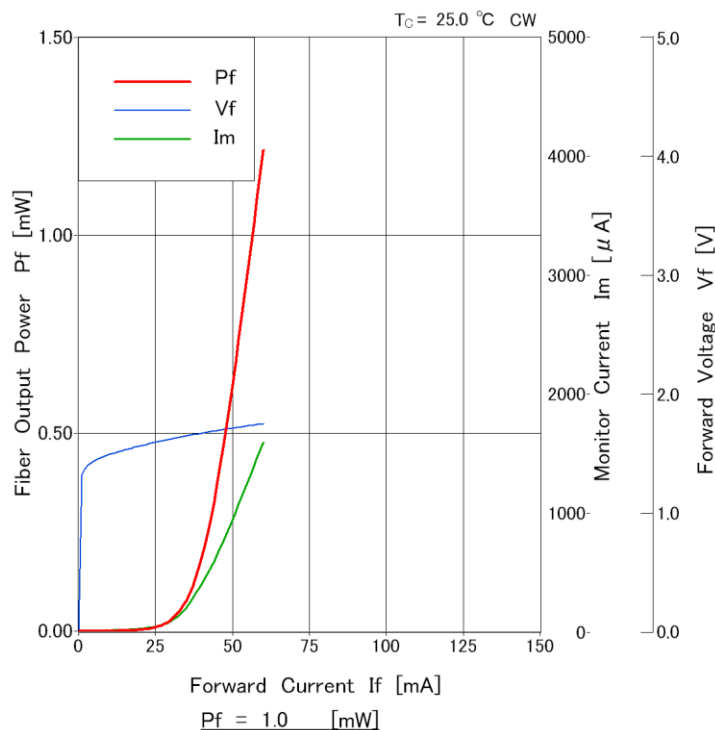
OPTICAL AND ELECTRICAL CHARACTERISTICS (T_C = 25°C)

Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Current	I _F	P _f = 1 mW	–	70	100	mA
Forward Voltage	V _F	P _f = 1 mW	–	2.0	2.5	V
Center Wavelength	λ _C	P _f = 1 mW	810	830	850	nm
Spectral Bandwidth	Δλ	P _f = 1 mW, -3 dB	10	15	–	nm
Spectral Modulation	M _d	P _f = 1 mW	–	2	10	%
PD Monitor Current	I _m	P _f = 1 mW, V _{RD} = 5 V	0.2	1.5	–	μA
Tracking Error	ΔP _f	I _m = const., T _C = -20 to +70°C	-2.0	–	2.0	dB

TYPICAL CHARACTERISTICS

Output Power/Forward Voltage/Monitor Current

Emission Spectrum





CAUTION : Handle the fiber of the enclosed device(s) with extreme care ; glass fiber is subject to breakage if mishandled and permanent damage to the device may result. Do not pull the device by the fiber or protective sleeve.
Do not coil the fiber into a loop of than 30 mm in radius.

SEMICONDUCTOR LASER

AVOID EXPOSURE
Invisible laser radiation is emitted from this aperture

DANGER

INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE TO
DIRECT OR SCATTERED RADIATION

OUTPUT POWER 500mW
WAVELENGTH 0.80 to 1.80 μ m
CLASS IIIb LASER PRODUCT

Caution - use of controls or adjustments or performance of procedures other than those specified herein may result in hazardous radiation exposure.
This Product Complies with 21 CFR 1040.10 and 1040.11
Manufactured Anritsu Corp. 5-1-1 Onna, Atsugi-shi, Kanagawa, Japan



ANRITSU CORPORATION

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Contact URL

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Please read "Notes on Handling Optical Devices" before use.

<https://www.anritsu.com/sensing-devices/guide/optdevices-handling>



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